

2-Lines, Uni-directional, Ultra-low Capacitance Transient Voltage Suppressors

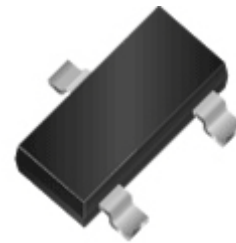
Descriptions

The ESD5302F is an ultra-low capacitance TVS (Transient Voltage Suppressor) array designed to protect high speed data interfaces. It has been specifically designed to protect sensitive electronic components which are connected to data and transmission lines from over-stress caused by ESD (Electrostatic Discharge).

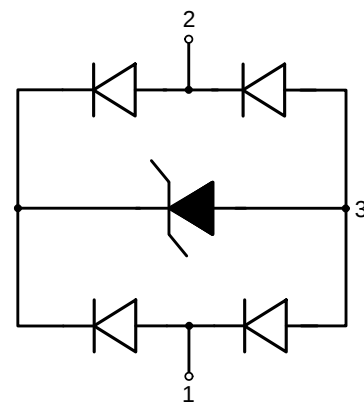
The ESD5302F incorporates two pairs of ultra- low capacitance steering diodes plus a TVS diode.

The ESD5302F may be used to provide ESD protection up to $\pm 20\text{kV}$ (contact and air discharge) according to IEC61000-4-2, and withstand peak pulse current up to 4A (8/20 μs) according to IEC61000-4-5.

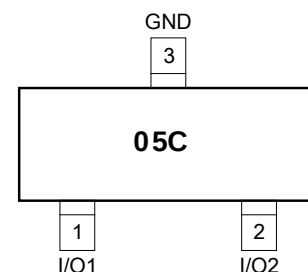
The ESD5302F is available in SOT-23 package. Standard products are Pb-free and Halogen-free.



SOT-23 (Top View)



Circuit diagram



Features

- Stand-off voltage: 5V Max
- Transient protection for each line according to IEC61000-4-2 (ESD): $\pm 20\text{kV}$ (contact and air discharge)
IEC61000-4-4 (EFT): 40A (5/50ns)
IEC61000-4-5 (surge): 4A (8/20 μs)
- Ultra-low capacitance: $C_J = 30\text{ pF typ.}$
- Ultra-low leakage current: $I_R < 1\text{ nA typ.}$
- Low clamping voltage: $V_{CL} = 20\text{V @ } I_{PP} = 16\text{A(TLP)}$
- Solid-state silicon technology

Order information

Device	Package	Shipping
ESD5302F	SOT-23	3000/Tape&Reel

Absolute maximum ratings

Parameter	Symbol	Rating	Unit
Peak pulse power ($t_p = 8/20\mu s$)	P_{pk}	60	W
Peak pulse current ($t_p = 8/20\mu s$)	I_{PP}	4	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 20	kV
ESD according to IEC61000-4-2 contact discharge		± 20	
Junction temperature	T_J	125	$^{\circ}C$
Operating temperature	T_{OP}	-40~85	$^{\circ}C$
Lead temperature	T_L	260	$^{\circ}C$
Storage temperature	T_{STG}	-55~150	$^{\circ}C$

Electrical characteristics ($T_A=25^{\circ}C$, unless otherwise noted)

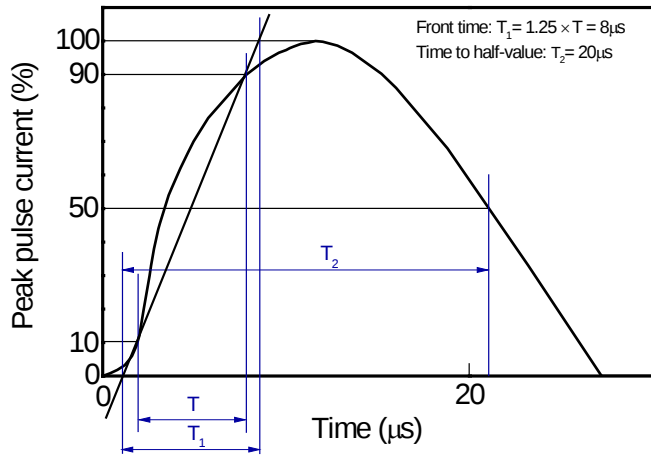
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse maximum working voltage	V_{RWM}				5.0	V
Reverse leakage current	I_R	$V_{RWM} = 5V$		<1	100	nA
Reverse breakdown voltage	V_{BR}	$I_T = 1mA$	7.0	8.0	9.0	V
Forward voltage	V_F	$I_T = 10mA$	0.6	0.9	1.2	V
Clamping voltage ¹⁾	V_{CL}	$I_{PP} = 16A, t_p = 100ns$		20		V
Dynamic resistance ¹⁾	R_{DYN}			0.65		Ω
Clamping voltage ²⁾	V_{CL}	$I_{PP} = 1A, t_p = 8/20\mu s$			11	V
		$I_{PP} = 4A, t_p = 8/20\mu s$			15	V
Junction capacitance	C_J	$V_R = 0V, f = 1MHz$ Any I/O pin to GND		30	50	pF
		$V_R = 0V, f = 1MHz$ Between any I/O pin		30	50	pF

Notes:

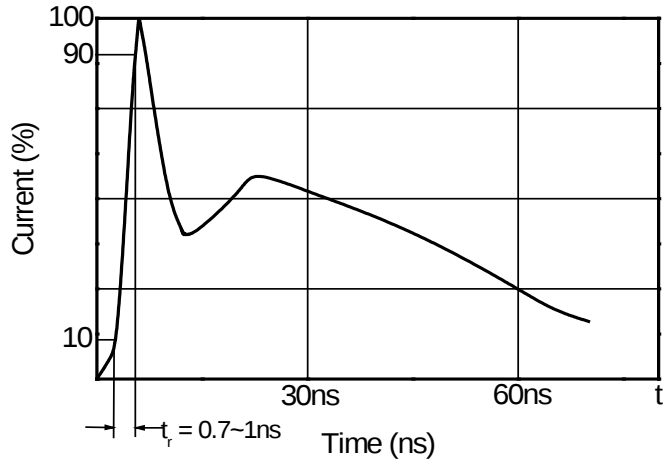
1) TLP parameter: $Z_0 = 50 \Omega$, $t_p = 100ns$, $t_r = 2ns$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.

2) According to IEC61000-4-5.

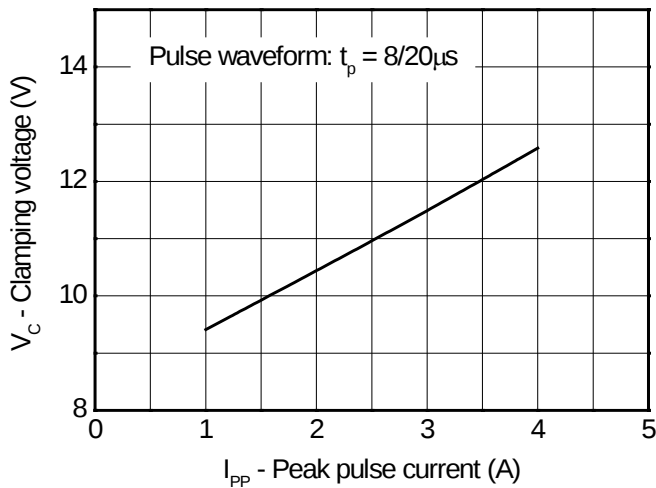
Typical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)



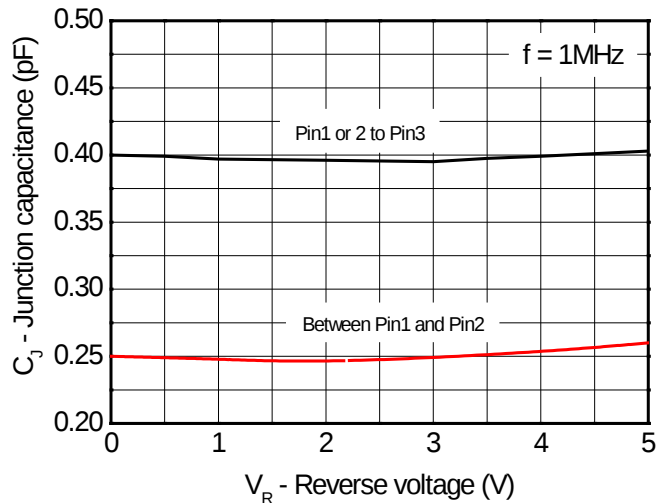
8/20 μs waveform per IEC61000-4-5



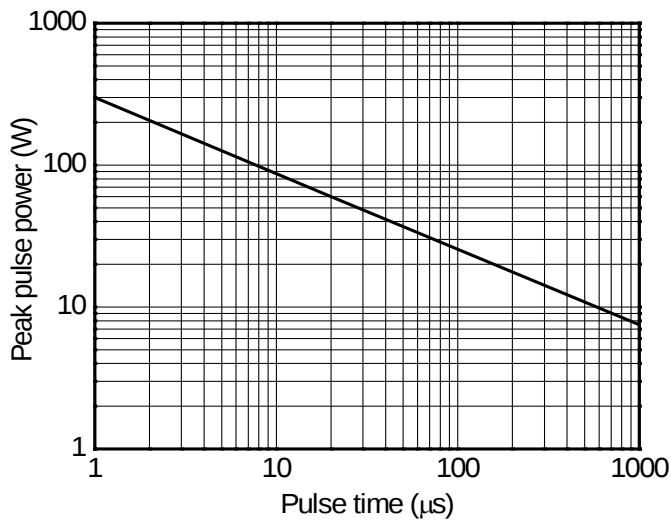
Contact discharge current waveform per IEC61000-4-2



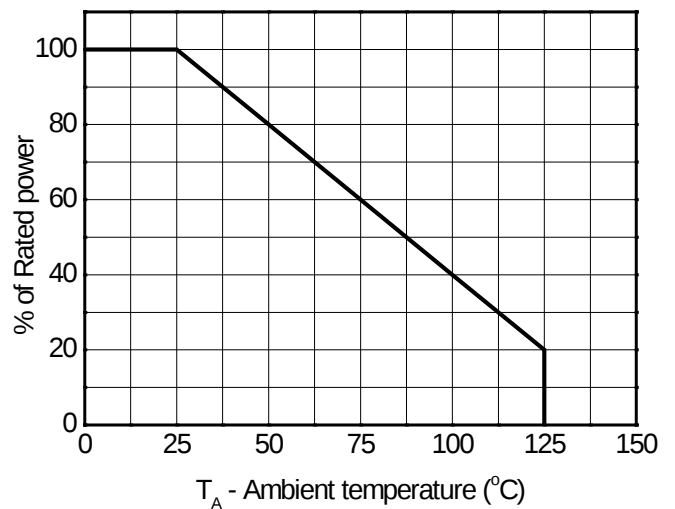
Clamping voltage vs. Peak pulse current



Capacitance vs. Reverse voltage

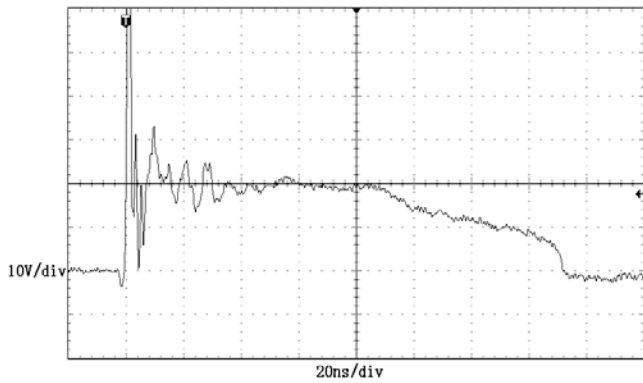


Non-repetitive peak pulse power vs. Pulse time

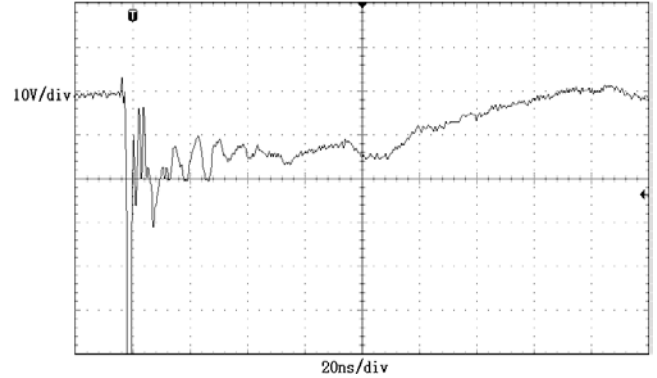


Power derating vs. Ambient temperature

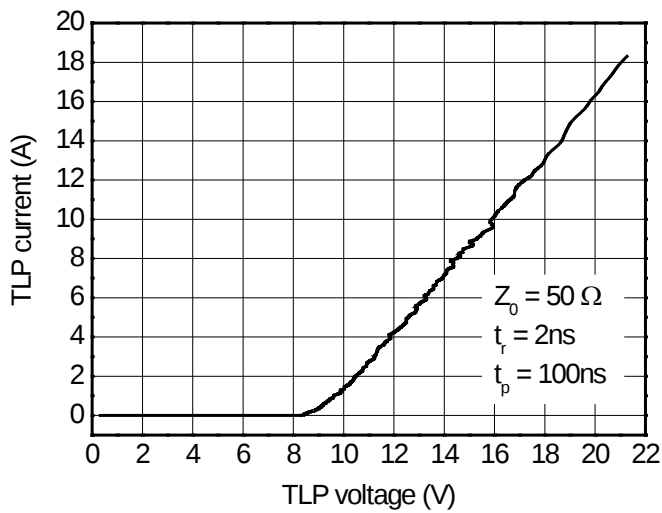
Typical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)



ESD clamping
(+8kV contact discharge per IEC61000-4-2)



ESD clamping
(-8kV contact discharge per IEC61000-4-2)



TLP Measurement